

Silicon NPN Power Transistors

2SC2258A

DESCRIPTION

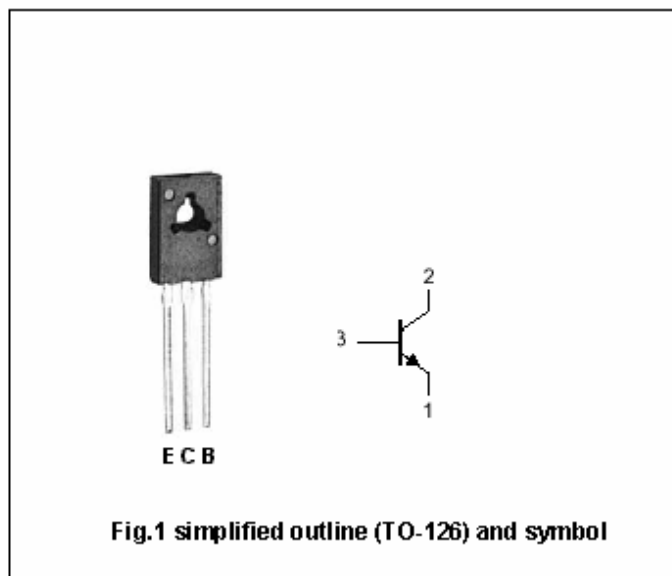
- With TO-126 package
- High transition frequency f_T
- High collector-emitter voltage V_{CEO}

APPLICATIONS

- High voltage general amplifier
- TV video output amplifier

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	300	V
V_{CEO}	Collector- emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		0.1	A
I_{CM}	Collector current-peak		0.15	A
P_C	Collector power dissipation	$T_C=25$	1.2^{*1}	W
			4^{*2}	
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55 ~ +150	

Note :*1: Without heat sink

*2: With a 100 × 100 × 2 mm A1 heat sink

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
I_{CER}	Collector cutoff current	$V_{CE}=250V; R_{BE}=100k\Omega$			100	μA
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=0.1mA; I_C=0$	7			V
V_{CESat}	Collector-emitter saturation voltage	$I_C=50mA; I_B=5mA$			1.2	V
V_{BE}	Base-emitter voltage	$I_C=40mA; V_{CE}=20V$			1.2	V
h_{FE-1}	DC current gain	$I_C=40mA; V_{CE}=20V$	40			
h_{FE-2}	DC current gain	$I_C=5mA; V_{CE}=50V$	30			
C_{OB}	Output capacitance	$I_E=0; V_{CB}=50V; f=1MHz$		3	4.5	pF
f_T	Transition frequency	$I_E=-10mA; V_{CE}=10V$		100		MHz

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PACKAGE OUTLINE

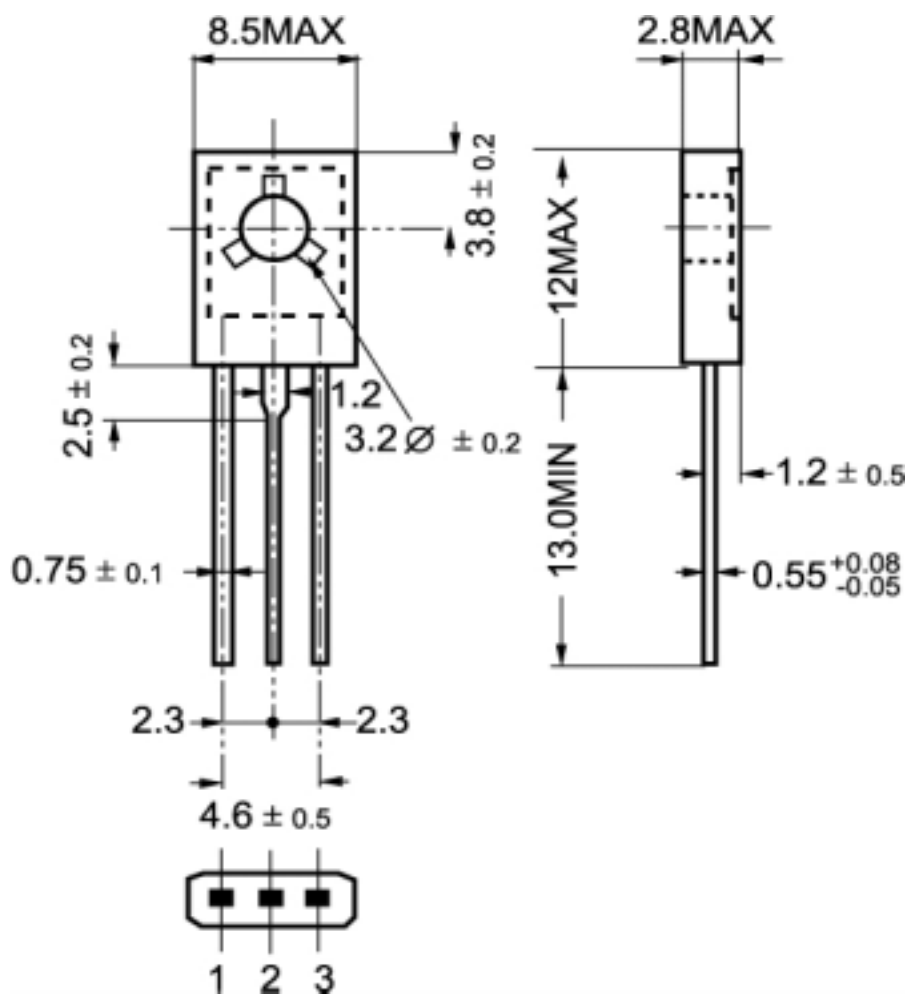


Fig.2 Outline dimensions